

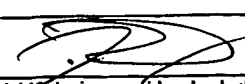
First Named Inventor	Kirk D. Prall	<b>INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</b>
Serial No.	10/738,408	
Filing Date	December 16, 2003	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	8316	
Attorney Docket No.	400.249US01	
Title: NROM MEMORY CELL, MEMORY ARRAY, RELATED DEVICES AND METHODS		Sheet 1 of 7

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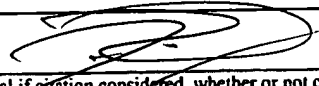
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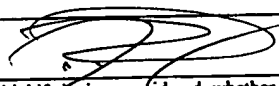
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First Named Inventor	Kirk D. Prall	<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</b>
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Examiner Name	Unknown	
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Examiner Initials	Document No.	Issue/Publication Date	Name	Filing Date
<i>B</i>	5,617,351	04/01/1997	Bertin	06/05/1995
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Examiner Initials	Foreign Patent		Name	Publication Date	Translation
	Country	No.			

Other References	
Examiner Initials	Author, Title, Date, Pages, etc.

Examiner Signature	<i>[Signature]</i>	Date Considered	12/21/05
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